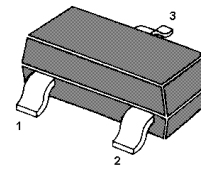


# MMBTSC2411

NPN Silicon Epitaxial Planar Transistor

SOT-23

The transistor is subdivided into three groups P, Q and R according to its DC current gain.



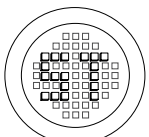
1.BASE 2.EMITTER 3.COLLECTOR  
SOT-23 Plastic Package

Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	40	V
Collector Emitter Voltage	$V_{CEO}$	32	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	500	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-55 to +150	$^\circ\text{C}$

Characteristics at  $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 3\text{ V}$ , $I_C = 100\text{ mA}$	P	$h_{FE}$	82	-	180	-
	Q	$h_{FE}$	120	-	270	-
	R	$h_{FE}$	180	-	390	-
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	40	-	-	V	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	32	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V	
Collector Cutoff Current at $V_{CB} = 20\text{ V}$	$I_{CBO}$	-	-	1	$\mu\text{A}$	
Emitter Cutoff Current at $V_{EB} = 4\text{ V}$	$I_{EBO}$	-	-	1	$\mu\text{A}$	
Collector Saturation Voltage at $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	-	0.4	V	
Transition frequency at $V_{CE} = 5\text{ V}$ , $-I_E = 20\text{ mA}$ , $f = 100\text{ MHz}$	$f_T$	-	250	-	MHz	
Output Capacitance at $V_{CB} = 10\text{ V}$ , $I_E = 0\text{ A}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	6	-	pF	



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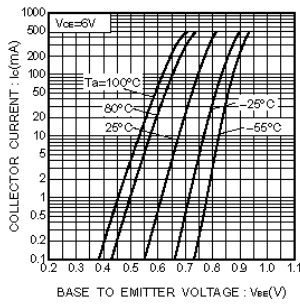


Fig.1 Grounded emitter propagation characteristics

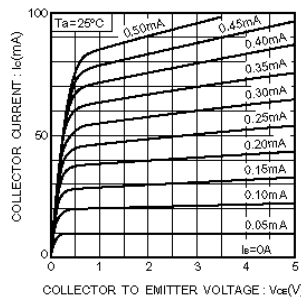


Fig.2 Grounded emitter output characteristics(I)

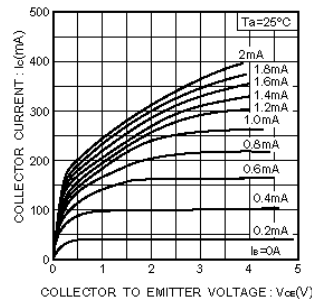


Fig.3 Grounded emitter output characteristics(II)

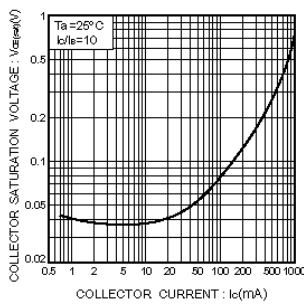


Fig.4 Collector-emitter saturation voltage vs. collector current

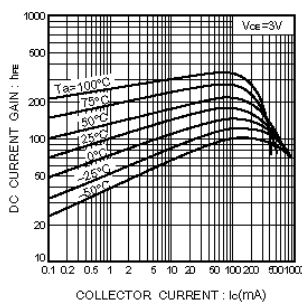


Fig.5 DC current gain vs. collector current

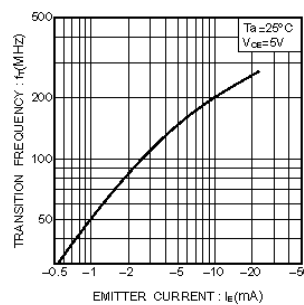


Fig.6 Gain bandwidth product vs. emitter current

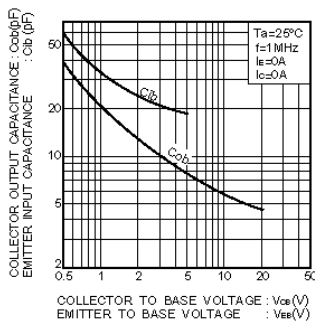


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage